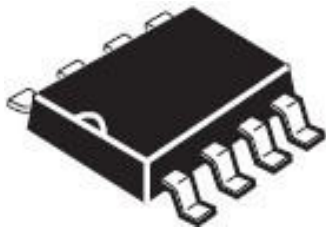


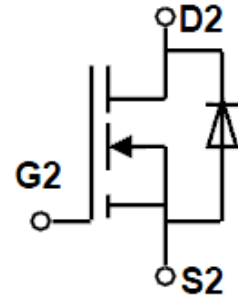
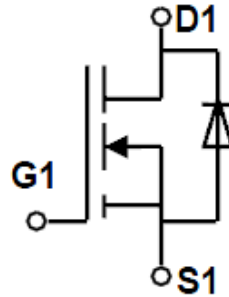
FEATURES

- ◆ Super high dense cell design for low $R_{DS(ON)}$.
- ◆ Rugged and reliable.
- ◆ SOP-8 package.
- ◆ Pb Free.

Product Summary		
V_{DS} (V)	I_D (A)	$R_{DS(ON)}$ (m Ω) Max
20V	6A	32 @ $V_{GS} = 4.0V$
		43 @ $V_{GS} = 2.5V$



SOP-8



ABSOLUTE MAXIMUM RATINGS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous @ $T_C = 25$ C	I_D	6	A
-Pulse d ^b	I_{DM}	35	A
Drain-Source Diode Forward Current ^a	I_S	1.7	A
Maximum Power Dissipation ^a	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	$^{\circ}C/W$
--	-----------------	------	---------------

ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typc	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.0V, I_D=6A$		25	32	m Ω
		$V_{GS}=2.5V, I_D=3A$		35	43	
On-State Drain Current	$I_{D(ON)}$	$V_{DS}=5V, V_{GS}=4V$	30			A
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=4A$		12		S
Input Capacitance	C_{ISS}	$V_{DS}=8V$		810		pF
Output Capacitance	C_{OSS}	$V_{GS}=0V$		155		
Reverse Transfer Capacitance	C_{RSS}	$f=1.0MHz$		125		
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=10V,$		18		ns
Rise Time	t_r	$I_D=1A,$		5		
Turn-Off Delay Time	$t_{D(OFF)}$	$V_{GEN}=4.5V,$		44		
Fall Time	t_f	$R_{GEN}=10\Omega,$ $R_L=10\Omega$		20		
Total Gate Charge	Q_g	$V_{DS}=10V,$		11		nC
Gate-Source Charge	Q_{gs}	$I_D=4A,$		3		
Gate-Drain Charge	Q_{gd}	$V_{GS}=4.5V$		2.5		
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_D=1A$		0.8	1.2	V

Notes:

- Surface Mounted on FR4 Board, $t \leq 10$ sec.
- Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

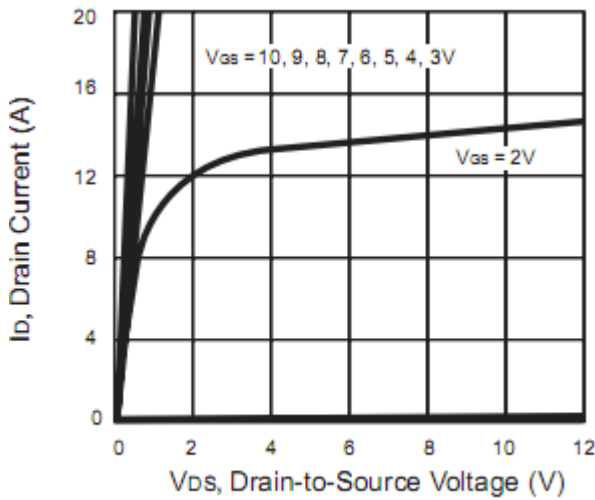


Figure 1. Output Characteristics

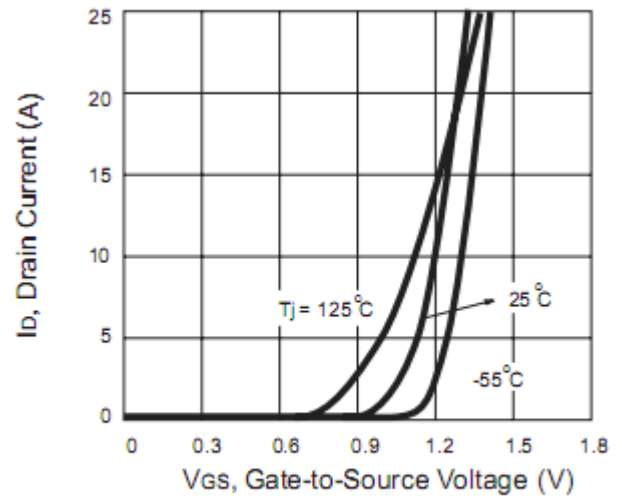


Figure 2. Transfer Characteristics

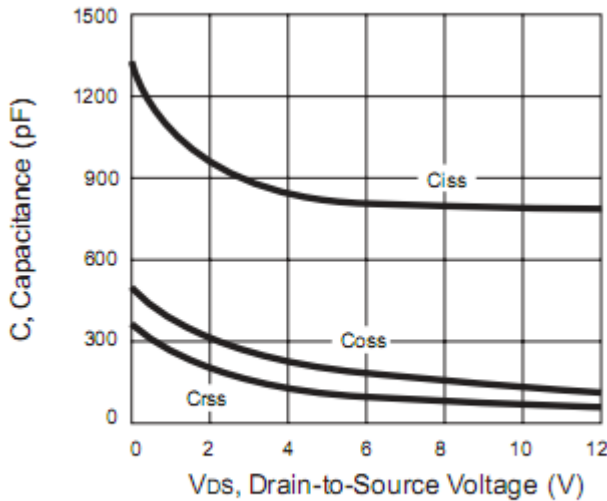


Figure 3. Capacitance

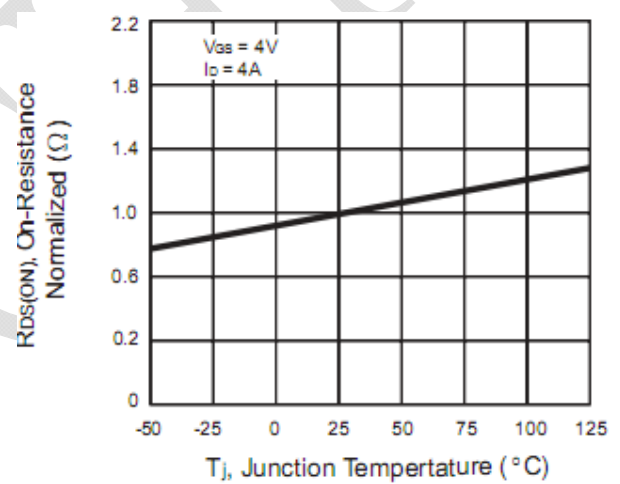


Figure 4. On-Resistance Variation with Temperature

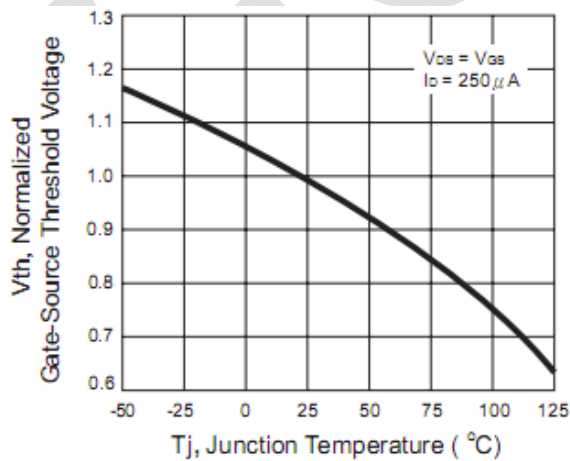


Figure 5. Gate Threshold Variation with Temperature

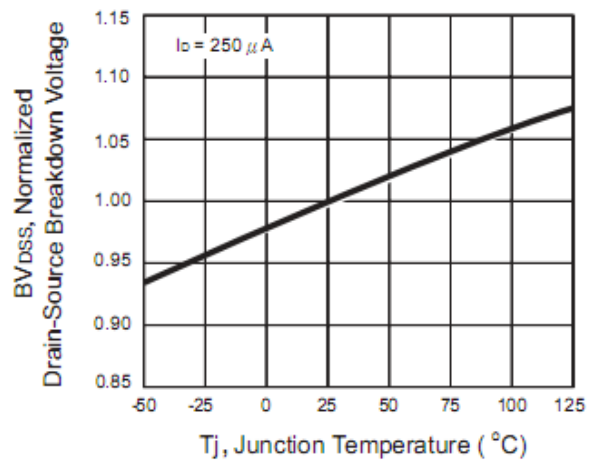


Figure 6. Breakdown Voltage Variation with Temperature

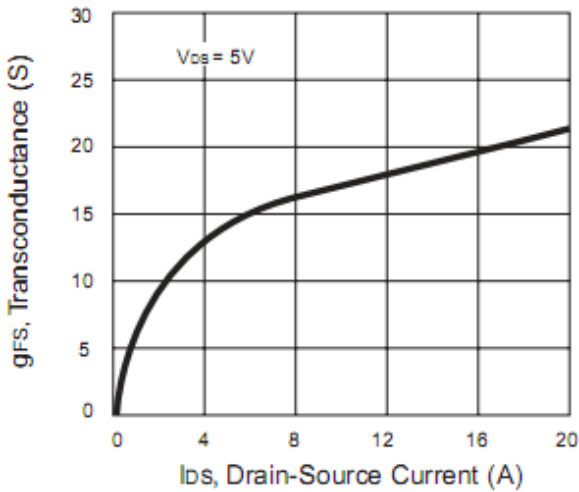


Figure 7. Transconductance Variation with Drain Current

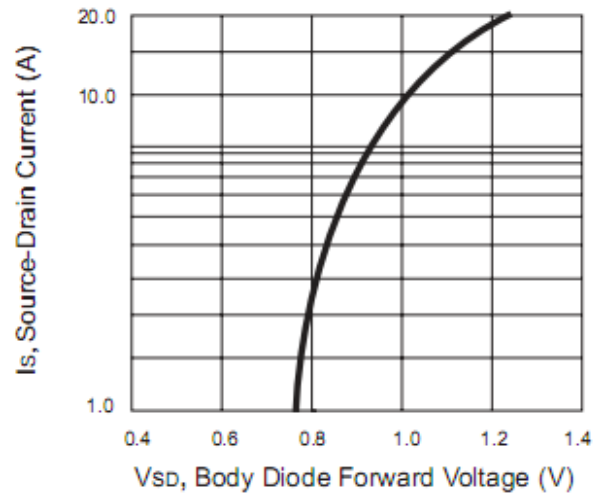


Figure 8. Body Diode Forward Voltage Variation with Source Current

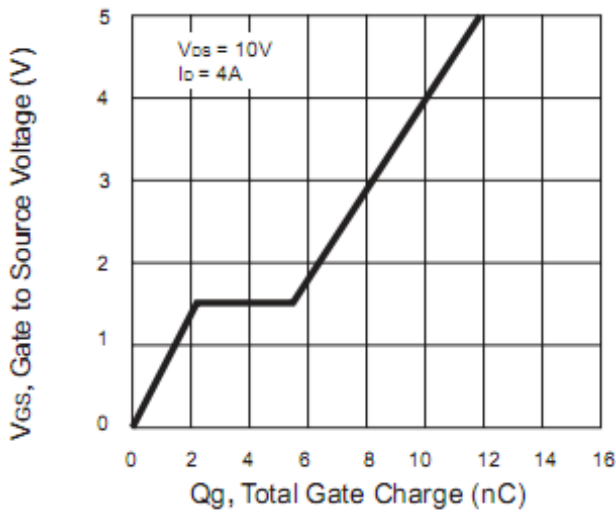


Figure 9. Gate Charge

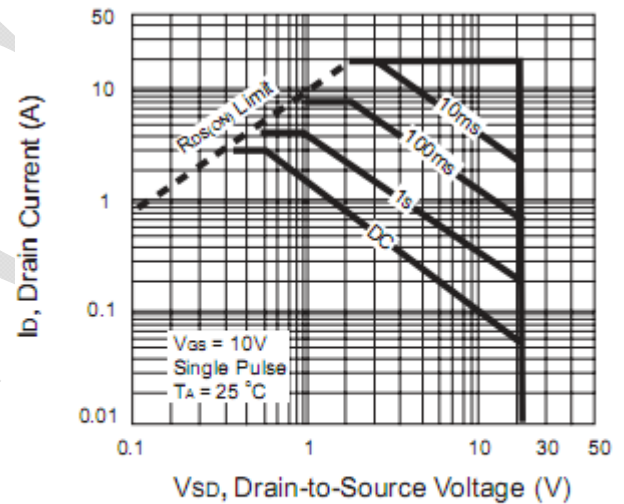


Figure 10. Maximum Safe Operating Area

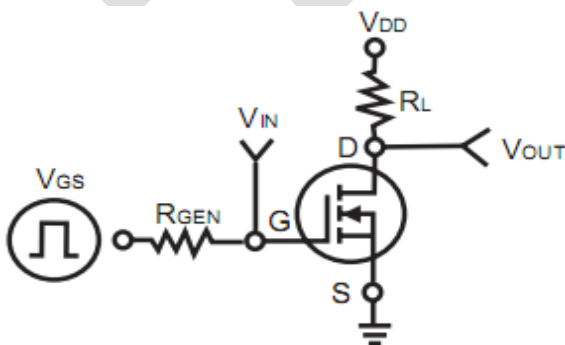


Figure 11. Switching Test Circuit

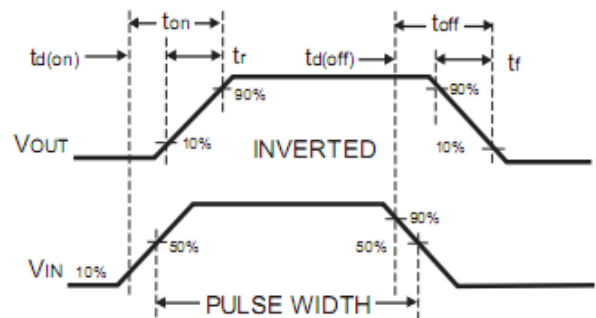


Figure 12. Switching Waveforms

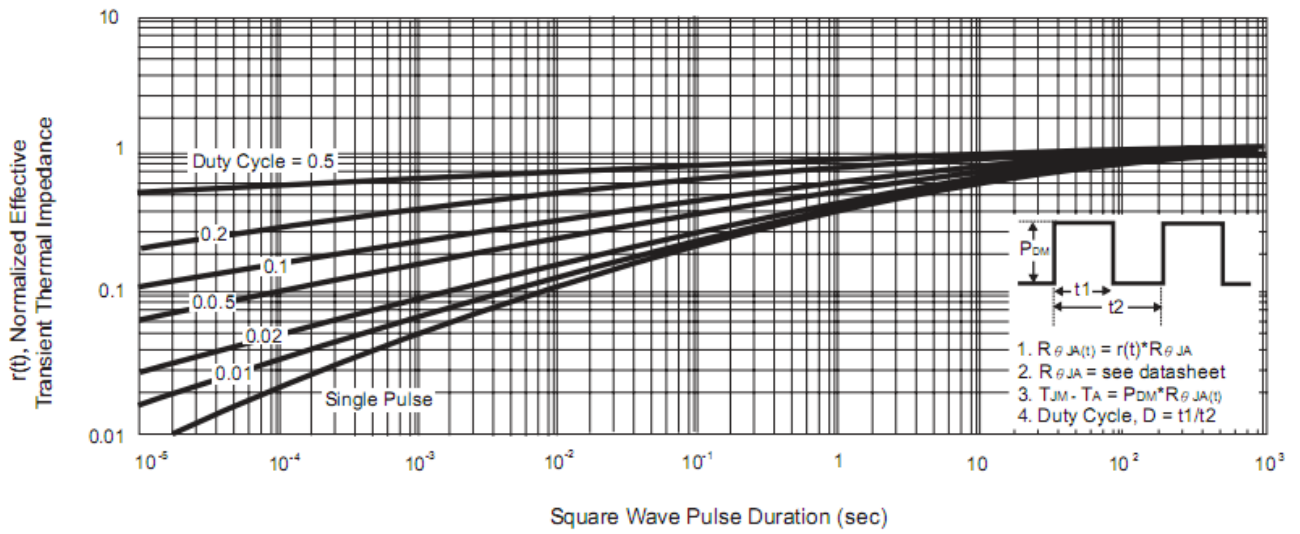


Figure 13. Normalized Thermal Transient Impedance Curve

HOTCHIP

Copyright © 2008 by HOTCHIP TECHNOLOGY CO., LTD.

The information appearing in this Data Sheet is believed to be accurate at the time of publication. However, HOTCHIP assumes no responsibility arising from the use of the specifications described. The applications mentioned herein are used solely for the purpose of illustration and HOTCHIP makes no warranty or representation that such applications will be suitable without further modification, nor recommends the use of its products for application that may present a risk to human life due to malfunction or otherwise. HOTCHIP's products are not authorized for use as critical components in life support devices or systems. HOTCHIP reserves the right to alter its products without prior notification. For the most up-to-date information, please visit our web site at <http://www.hotchip.net.cn>.